

勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787

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LMC662

CMOS Dual Operational Amplifier

General Description

The LMC662 CMOS Dual operational amplifier is ideal for operation from a single supply. It operates from +5V to +15V and features rail-to-rail output swing in addition to an input common-mode range that includes ground. Performance limitations that have plagued CMOS amplifiers in the past are not a problem with this design. Input $V_{\rm OS}$, drift, and broadband noise as well as voltage gain into realistic loads (2 $\rm k\Omega$ and $600\Omega)$ are all equal to or better than widely accepted bipolar equivalents.

This chip is built with National's advanced Double-Poly Silicon-Gate CMOS process.

See the LMC660 datasheet for a Quad CMOS operational amplifier with these same features.

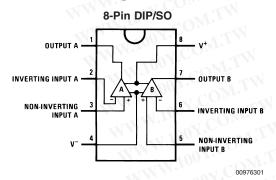
Features

- Rail-to-rail output swing
- Specified for 2 kΩ and 600Ω loads
- High voltage gain: 126 dB
- Low input offset voltage: 3 mV
- Low offset voltage drift: 1.3 µV/°C
- Ultra low input bias current: 2 fA
- Input common-mode range includes V
- Operating range from +5V to +15V supply
- I_{SS} = 400 μA/amplifier; independent of V+
- Low distortion: 0.01% at 10 kHz
- Slew rate: 1.1 V/µs

Applications

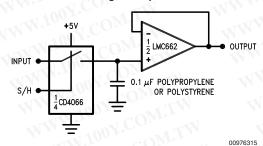
- High-impedance buffer or preamplifier
- Precision current-to-voltage converter
- Long-term integrator
- Sample-and-hold circuit
- Peak detector
- Medical instrumentation
- Industrial controls
- Automotive sensors

Connection Diagram



Typical Application

Low-Leakage Sample-and-Hold



Ordering Information

Package	Temperature Range		NSC	Transport
WV	Industrial	Commercial	Drawing	Media
8-Pin	LMC662AIM	LMC662CM	M08A	Rail
Small Outline	LMC662AIMX	LMC662CMX		Tape and Reel
8-Pin	LMC662AIN	LMC662CN	N08E	Rail
Molded DIP	MW W.			

Absolute Maximum Ratings (Note 3)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

 $\begin{array}{lll} \mbox{Differential Input Voltage} & \pm \mbox{Supply Voltage} \\ \mbox{Supply Voltage } (V^+ - V^-) & 16V \\ \mbox{Output Short Circuit to } V^+ & (\mbox{Note 12}) \\ \mbox{Output Short Circuit to } V^- & (\mbox{Note 1}) \\ \end{array}$

Lead Temperature

(Soldering, 10 sec.) 260°C Storage Temp. Range –65°C to +150°C

Voltage at Input/Output Pins (V^+) +0.3V, (V^-) -0.3V

Current at Output Pin ±18 mA

Current at Input Pin ±5 mA

Current at Power Supply Pin 35 m/s

Power Dissipation (Note 2)

Junction Temperature 150°C

ESD Tolerance (Note 8) 1000V

Operating Ratings(Note 3)

Temperature Range

 $\begin{array}{lll} LMC662AI & -40^{\circ}C \leq T_{J} \leq +85^{\circ}C \\ LMC662C & 0^{\circ}C \leq T_{J} \leq +70^{\circ}C \\ \\ Supply \ Voltage \ Range & 4.75V \ to \ 15.5V \\ \\ Power \ Dissipation & (Note \ 10) \\ \end{array}$

Thermal Resistance (θ_{JA}) (Note 11)

8-Pin Molded DIP 101°C/W 8-Pin SO 165°C/W

DC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for $T_J = 25^{\circ}C$. **Boldface** limits apply at the temperature extremes. $V^+ = 5V$, $V^- = 0V$, $V_{CM} = 1.5V$, $V_O = 2.5V$ and $R_L > 1M$ unless otherwise specified.

Parameter	Conditions	Typ (Note 4)	Limit (Note 4)	Limit (Note 4)	Units
	WWW.	LOW.COM	3.3	6.3	max
Input Offset Voltage Average Drift	M.TW WWY	1.3	LTV	MMM.1002	μV/°C
Input Bias Current	OM.TW WW	0.002	M.T.V	2 1.100	pA max
Input Offset Current	COM.TW W	0.001	2	WWW.I	pA max
Input Resistance	COMMENT	>1 00%	CONTRA	MM	TeraΩ
Common Mode	$0V \le V_{CM} \le 12.0V$	83	CO 70	63	dB
Rejection Ratio	V ⁺ = 15V	W.100	68	62	min
Positive Power Supply	5V ≤ V ⁺ ≤ 15V	83	70	63	dB
Rejection Ratio	$V_{O} = 2.5V$	WWW	68	62	min
Negative Power Supply	0V ≤ V ⁻ ≤ −10V	94	84	74	dB
Rejection Ratio	1001. COM.T.	W.	83	73	min
Input Common-Mode	V ⁺ = 5V & 15V	-0.4	-0.1	-0.1	V 1
Voltage Range	For CMRR ≥ 50 dB	WW.	100/0	TW 0	max
	W.100X.COM.TW	V ⁺ – 1.9	V ⁺ - 2.3 V ⁺ - 2.5	V ⁺ - 2.3 V ⁺ - 2.4	V min
Large Signal	$R_L = 2 k\Omega \text{ (Note 5)}$	2000	440	300	V/mV
Voltage Gain	Sourcing	W W	400	200	min
	Sinking	500	180	90	V/mV
	W. Tay 100 Y.	. A.	120	80	min
	$R_L = 600\Omega \text{ (Note 5)}$	1000	220	150	V/mV
	Sourcing		200	100	min
	Sinking	250	100 60	50 40	V/mV min

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DC Electrical Characteristics (Continued)

Unless otherwise specified, all limits guaranteed for $T_J = 25^{\circ}C$. **Boldface** limits apply at the temperature extremes. $V^+ = 5V$, $V^- = 0V$, $V_{CM} = 1.5V$, $V_O = 2.5V$ and $R_L > 1M$ unless otherwise specified.

Parameter	Conditions	Typ (Note 4)	Limit (Note 4)	Limit (Note 4)	Units
$R_L = 2 k\Omega \text{ to } V^+/2$		4.79	4.76	min	
	WWW. 1007	0.10	0.15	0.19	V
	WWW.Io		0.17	0.21	max
	V ⁺ = 5V	4.61	4.41	4.27	V
	$R_L = 600\Omega \text{ to V}^{+}/2$		4.31	4.21	min
	WWW.	0.30	0.50	0.63	V
	M. T. T. T. W. F.		0.56	0.69	max
	V ⁺ = 15V	14.63	14.50	14.37	COLA
	$R_L = 2 k\Omega \text{ to } V^+/2$		14.44	14.32	min
	CONT. TIM	0.26	0.35	0.44	V
	COM.		0.40	0.48	max
	V ⁺ = 15V	13.90	13.35	12.92	V
	$R_L = 600\Omega \text{ to V}^{+}/2$		13.15	12.76	min
	V CONT.	0.79	1.16	1.45	V
	COM		1.32	1.58	max
Output Current	Sourcing, V _O = 0V	22	16	13	mA
V+ = 5V	ON.CO.		14	11	min
	Sinking, V _O = 5V	21	.0 16	13	mA
	1100 r. COM:1		14	11	min
Output Current	Sourcing, V _O = 0V	40	28	23	mA
V ⁺ = 15V	W. CON.CO. STW		25	21	min
	Sinking, V _O = 13V	39	28	23	mA
	(Note 12)		24	20	min
Supply Current	Both Amplifiers	0.75	10/1.3	1.6	mA
	V _O = 1.5V		1.5	1.8	max

AC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for $T_J = 25^{\circ}C$. **Boldface** limits apply at the temperature extremes. $V^+ = 5V$, $V^- = 0V$, $V_{CM} = 1.5V$, $V_O = 2.5V$ and $R_L > 1M$ unless otherwise specified.

Parameter	Conditions	Typ (Note 4)	Limit (Note 4)	Limit (Note 4)	Units
		TIN			
Slew Rate	(Note 6)	1.1	0.8	0.8	V/µs
	W. 1001.	OW.T.	0.6	0.7	min
Gain-Bandwidth Product	MM. 1007.0	1.4	1/1/1		MHz
Phase Margin	WWW.	50			Deg
Gain Margin	M.In.	ON 17			dB
Amp-to-Amp Isolation	(Note 7)	130			dB
Input-Referred Voltage Noise	F = 1 kHz	22			nV/√ Hz
Input-Referred Current Noise	F = 1 kHz	0.0002			pA/√ Hz

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AC Electrical Characteristics (Continued)

Unless otherwise specified, all limits guaranteed for $T_J = 25^{\circ}C$. **Boldface** limits apply at the temperature extremes. $V^+ = 5V$, $V^- = 0V$, $V_{CM} = 1.5V$, $V_O = 2.5V$ and $R_L > 1M$ unless otherwise specified.

Parameter	Conditions	Typ (Note 4)	LMC662AI	Limit (Note 4)	Units
	NW.100Y.COM.TW	WW	Limit (Note 4)		
Total Harmonic Distortion	$F = 10 \text{ kHz}, A_V = -10$ $R_L = 2 \text{ k}\Omega, V_O = 8 \text{ V}_{PP}$ $V^+ = 15V$	0.01	MM.100X.	COM.TW	%

Note 1: Applies to both single-supply and split-supply operation. Continuous short circuit operation at elevated ambient temperature and/or multiple Op Amp shorts can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of ±30 mA over long term may adversely affect reliability.

Note 2: The maximum power dissipation is a function of $T_{J(max)}$, θ_{JA} , and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(max)} - T_A)/\theta_{JA}$.

Note 3: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed.

Note 4: Typical values represent the most likely parametric norm. Limits are guaranteed by testing or correlation.

Note 5: $V^+ = 15V$, $V_{CM} = 7.5V$ and R_L connected to 7.5V. For Sourcing tests, $7.5V \le V_O \le 11.5V$. For Sinking tests, $2.5V \le V_O \le 7.5V$.

Note 6: V+ = 15V. Connected as Voltage Follower with 10V step input. Number specified is the slower of the positive and negative slew rates.

Note 7: Input referred. V+ = 15V and R_L = 10 kΩ connected to V+/2. Each amp excited in turn with 1 kHz to produce V_O = 13 V_{PP}.

Note 8: Human body model, 1.5 k Ω in series with 100 pF.

Note 9: A military RETS electrical test specification is available on request.

Note 10: For operating at elevated temperatures the device must be derated based on the thermal resistance θ_{JA} with $P_D = (T_J - T_A)/\theta_{JA}$.

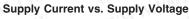
Note 11: All numbers apply for packages soldered directly into a PC board.

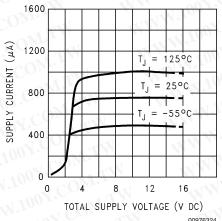
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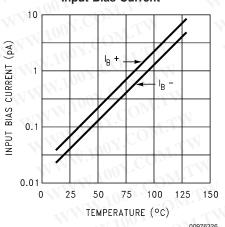
Note 12: Do not connect output to V^+ when V^+ is greater than 13V or reliability may be adversely affected.

Typical Performance Characteristics $V_S = \pm 7.5V$, $T_A = 25^{\circ}C$ unless otherwise specified

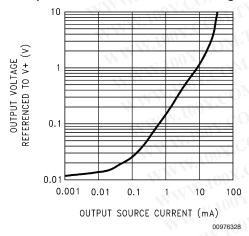




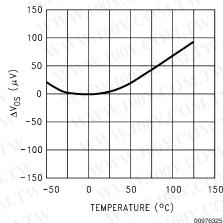
Input Bias Current



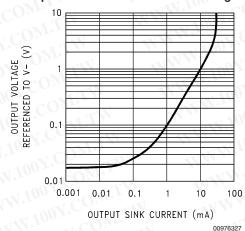
Output Characteristics Current Sourcing



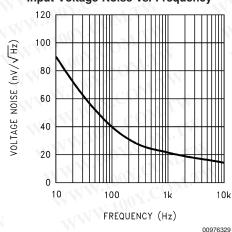
Offset Voltage



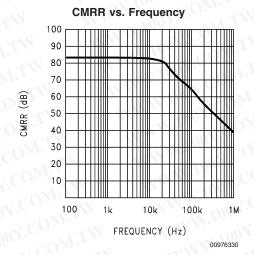
Output Characteristics Current Sinking



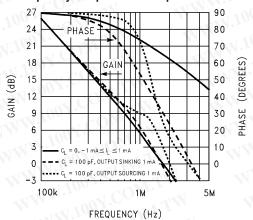
Input Voltage Noise vs. Frequency



Typical Performance Characteristics $V_S = \pm 7.5V$, $T_A = 25^{\circ}C$ unless otherwise specified (Continued)

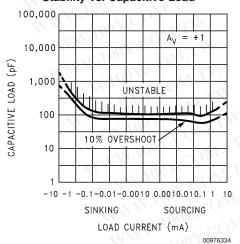


Frequency Response vs. Capacitive Load



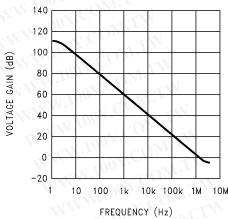
Stability vs. Capacitive Load

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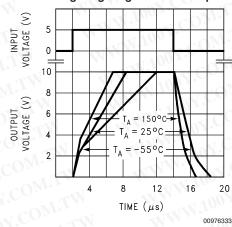


Note: Avoid resistive loads of less than 500Ω , as they may cause instability.

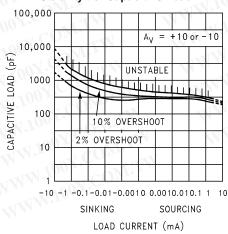
Open-Loop Frequency Response



Non-Inverting Large Signal Pulse Response



Stability vs. Capacitive Load



Note: Avoid resistive loads of less than 500Ω , as they may cause instability.

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Application Hints

AMPLIFIER TOPOLOGY

The topology chosen for the LMC662, shown in *Figure 1*, is unconventional (compared to general-purpose op amps) in that the traditional unity-gain buffer output stage is not used; instead, the output is taken directly from the output of the integrator, to allow rail-to-rail output swing. Since the buffer traditionally delivers the power to the load, while maintaining high op amp gain and stability, and must withstand shorts to either rail, these tasks now fall to the integrator.

As a result of these demands, the integrator is a compound affair with an embedded gain stage that is doubly fed forward (via $C_{\rm f}$ and $C_{\rm ff}$) by a dedicated unity-gain compensation driver. In addition, the output portion of the integrator is a push-pull configuration for delivering heavy loads. While sinking current the whole amplifier path consists of three gain stages with one stage fed forward, whereas while sourcing the path contains four gain stages with two fed forward.

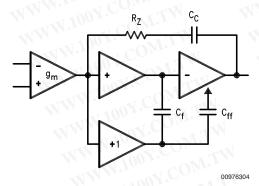


FIGURE 1. LMC662 Circuit Topology (Each Amplifier)

The large signal voltage gain while sourcing is comparable to traditional bipolar op amps, even with a 600Ω load. The gain while sinking is higher than most CMOS op amps, due to the additional gain stage; however, under heavy load (600Ω) the gain will be reduced as indicated in the Electrical Characteristics.

COMPENSATING INPUT CAPACITANCE

The high input resistance of the LMC662 op amps allows the use of large feedback and source resistor values without losing gain accuracy due to loading. However, the circuit will be especially sensitive to its layout when these large-value resistors are used.

Every amplifier has some capacitance between each input and AC ground, and also some differential capacitance between the inputs. When the feedback network around an amplifier is resistive, this input capacitance (along with any additional capacitance due to circuit board traces, the socket, etc.) and the feedback resistors create a pole in the feedback path. In the following General Operational Amplifier Circuit, *Figure 2*, the frequency of this pole is

$$f_p = \frac{1}{2\pi C_S R_P}$$

where $C_{\rm S}$ is the total capacitance at the inverting input, including amplifier input capacitance and any stray capacitance from the IC socket (if one is used), circuit board traces,

etc., and R_P is the parallel combination of R_F and R_{IN} . This formula, as well as all formulae derived below, apply to inverting and non-inverting op-amp configurations.

When the feedback resistors are smaller than a few $k\Omega$, the frequency of the feedback pole will be quite high, since C_S is generally less than 10 pF. If the frequency of the feedback pole is much higher than the "ideal" closed-loop bandwidth (the nominal closed-loop bandwidth in the absence of C_S), the pole will have a negligible effect on stability, as it will add only a small amount of phase shift.

However, if the feedback pole is less than approximately 6 to 10 times the "ideal" -3 dB frequency, a feedback capacitor, C_F , should be connected between the output and the inverting input of the op amp. This condition can also be stated in terms of the amplifier's low-frequency noise gain: To maintain stability, a feedback capacitor will probably be needed if

$$\left(\frac{\mathsf{R}_{\mathsf{F}}}{\mathsf{R}_{\mathsf{IN}}} + 1\right) \leq \sqrt{6 \times 2\pi \times \mathsf{GBW} \times \mathsf{R}_{\mathsf{F}} \times \mathsf{C}_{\mathsf{S}}}$$

where

$$\left(\frac{R_F}{R_{IN}} + 1\right)$$

is the amplifier's low-frequency noise gain and GBW is the amplifier's gain bandwidth product. An amplifier's low-frequency noise gain is represented by the formula

$$\left(\frac{R_F}{R_{IN}} + 1\right)$$

regardless of whether the amplifier is being used in an inverting or non-inverting mode. Note that a feedback capacitor is more likely to be needed when the noise gain is low and/or the feedback resistor is large.

If the above condition is met (indicating a feedback capacitor will probably be needed), and the noise gain is large enough that:

$$\left(\frac{\mathsf{R}_{\mathsf{F}}}{\mathsf{R}_{\mathsf{IN}}} + 1\right) \geq 2\sqrt{\mathsf{GBW} \times \mathsf{R}_{\mathsf{F}} \times \mathsf{C}_{\mathsf{S}}}$$

the following value of feedback capacitor is recommended:

$$C_{F} = \frac{C_{S}}{2\left(\frac{R_{F}}{R_{IN}} + 1\right)}$$

If

$$\left(\frac{\mathsf{R}_{\mathsf{F}}}{\mathsf{R}_{\mathsf{IN}}} + 1\right) < 2\sqrt{\mathsf{GBW} \times \mathsf{R}_{\mathsf{F}} \times \mathsf{C}_{\mathsf{S}}} \;,$$

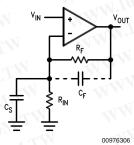
the feedback capacitor should be:

$$C_F = \sqrt{\frac{C_S}{GBW \times R_F}}$$

Application Hints (Continued)

Note that these capacitor values are usually significantly smaller than those given by the older, more conservative formula:

$$C_F = \frac{C_S\,R_{IN}}{R_F}$$



 C_S consists of the amplifier's input capacitance plus any stray capacitance from the circuit board and socket. C_F compensates for the pole caused by C_S and the feedback resistor.

FIGURE 2. General Operational Amplifier Circuit

Using the smaller capacitors will give much higher bandwidth with little degradation of transient response. It may be necessary in any of the above cases to use a somewhat larger feedback capacitor to allow for unexpected stray capacitance, or to tolerate additional phase shifts in the loop, or excessive capacitive load, or to decrease the noise or bandwidth, or simply because the particular circuit implementation needs more feedback capacitance to be sufficiently stable. For example, a printed circuit board's stray capacitance may be larger or smaller than the breadboard's, so the actual optimum value for $C_{\rm F}$ may be different from the one estimated using the breadboard. In most cases, the value of $C_{\rm F}$ should be checked on the actual circuit, starting with the computed value.

CAPACITIVE LOAD TOLERANCE

Like many other op amps, the LMC662 may oscillate when its applied load appears capacitive. The threshold of oscillation varies both with load and circuit gain. The configuration most sensitive to oscillation is a unity-gain follower. See the Typical Performance Characteristics.

The load capacitance interacts with the op amp's output resistance to create an additional pole. If this pole frequency is sufficiently low, it will degrade the op amp's phase margin so that the amplifier is no longer stable at low gains. As shown in *Figure 3*, the addition of a small resistor (50 Ω to 100 Ω) in series with the op amp's output, and a capacitor (5 pF to 10 pF) from inverting input to output pins, returns the phase margin to a safe value without interfering with lower-frequency circuit operation. Thus, larger values of capacitance can be tolerated without oscillation. Note that in all cases, the output will ring heavily when the load capacitance is near the threshold for oscillation.

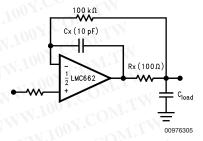


FIGURE 3. Rx, Cx Improve Capacitive Load Tolerance

Capacitive load driving capability is enhanced by using a pull up resistor to V⁺ Figure~4. Typically a pull up resistor conducting 500 μ A or more will significantly improve capacitive load responses. The value of the pull up resistor must be determined based on the current sinking capability of the amplifier with respect to the desired output swing. Open loop gain of the amplifier can also be affected by the pull up resistor (see Electrical Characteristics).

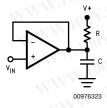


FIGURE 4. Compensating for Large Capacitive Loads with a Pull Up Resistor

PRINTED-CIRCUIT-BOARD LAYOUT FOR HIGH-IMPEDANCE WORK

It is generally recognized that any circuit which must operate with less than 1000 pA of leakage current requires special layout of the PC board. When one wishes to take advantage of the ultra-low bias current of the LMC662, typically less than 0.04 pA, it is essential to have an excellent layout. Fortunately, the techniques for obtaining low leakages are quite simple. First, the user must not ignore the surface leakage of the PC board, even though it may sometimes appear acceptably low, because under conditions of high humidity or dust or contamination, the surface leakage will be appreciable.

To minimize the effect of any surface leakage, lay out a ring of foil completely surrounding the LMC662's inputs and the terminals of capacitors, diodes, conductors, resistors, relay terminals, etc. connected to the op-amp's inputs. See Figure 5. To have a significant effect, guard rings should be placed on both the top and bottom of the PC board. This PC foil must then be connected to a voltage which is at the same voltage as the amplifier inputs, since no leakage current can flow between two points at the same potential. For example, a PC board trace-to-pad resistance of $10^{12}\Omega$, which is normally considered a very large resistance, could leak 5 pA if the trace were a 5V bus adjacent to the pad of an input. This would cause a 100 times degradation from the LMC662's actual performance. However, if a guard ring is held within 5 mV of the inputs, then even a resistance of $10^{11}\Omega$ would cause only 0.05 pA of leakage current, or perhaps a minor (2:1) degradation of the amplifier's performance. See Figures 6, 7, 8 for typical connections of guard rings for stan-

Application Hints (Continued)

dard op-amp configurations. If both inputs are active and at high impedance, the guard can be tied to ground and still provide some protection; see *Figure 9*.

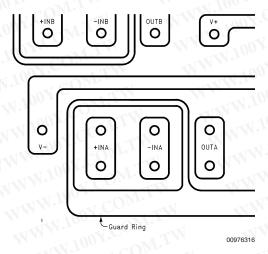


FIGURE 5. Example, using the LMC660, of Guard Ring in P.C. Board Layout

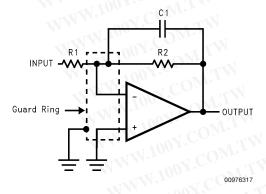


FIGURE 6. Guard Ring Connections: Inverting Amplifier

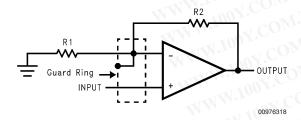


FIGURE 7. Guard Ring Connections: Non-Inverting Amplifier

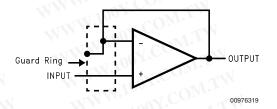


FIGURE 8. Guard Ring Connections: Follower

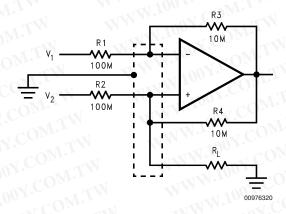
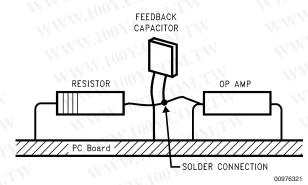


FIGURE 9. Guard Ring Connections: Howland Current Pump

The designer should be aware that when it is inappropriate to lay out a PC board for the sake of just a few circuits, there is another technique which is even better than a guard ring on a PC board: Don't insert the amplifier's input pin into the board at all, but bend it up in the air and use only air as an insulator. Air is an excellent insulator. In this case you may have to forego some of the advantages of PC board construction, but the advantages are sometimes well worth the effort of using point-to-point up-in-the-air wiring. See *Figure 10*.



(Input pins are lifted out of PC board and soldered directly to components. All other pins connected to PC board.)

FIGURE 10. Air Wiring

Application Hints (Continued)

BIAS CURRENT TESTING

The test method of *Figure 11* is appropriate for bench-testing bias current with reasonable accuracy. To understand its operation, first close switch S2 momentarily. When S2 is opened, then

$$I_b^- = \frac{dV_{OUT}}{dt} \times C2.$$

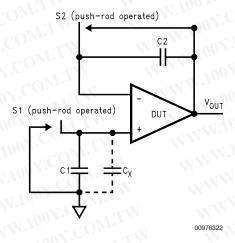


FIGURE 11. Simple Input Bias Current Test Circuit

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A suitable capacitor for C2 would be a 5 pF or 10 pF silver mica, NPO ceramic, or air-dielectric. When determining the magnitude of I_b –, the leakage of the capacitor and socket must be taken into account. Switch S2 should be left shorted most of the time, or else the dielectric absorption of the capacitor C2 could cause errors.

Similarly, if S1 is shorted momentarily (while leaving S2 shorted)

$$I_b{}^+ = \frac{dV_{OUT}}{dt} \times (C1 + C_x)$$

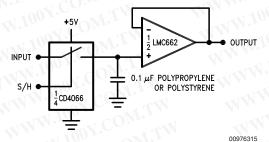
where Cx is the stray capacitance at the + input.

Typical Single-Supply Applications

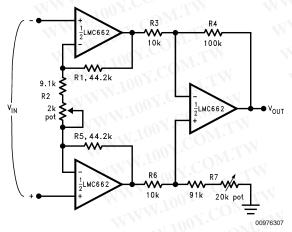
 $(V^+ = 5.0 V_{DC})$

Additional single-supply applications ideas can be found in the LM358 datasheet. The LMC662 is pin-for-pin compatible with the LM358 and offers greater bandwidth and input resistance over the LM358. These features will improve the performance of many existing single-supply applications. Note, however, that the supply voltage range of the LM662 is smaller than that of the LM358.

Low-Leakage Sample-and-Hold



Instrumentation Amplifier

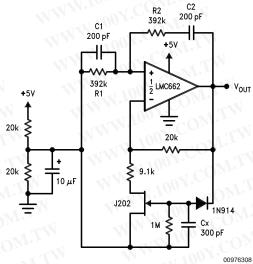


If R₁ = R₅, R₃ = R₆, and R₄ = R₇; then
$$\frac{V_{OUT}}{V_{IN}} = \frac{R2 + 2R1}{R2} \times \frac{R4}{R3}$$

 \therefore A_V \approx 100 for circuit shown.

For good CMRR over temperature, low drift resistors should be used. Matching of R3 to R6 and R4 to R7 affects CMRR. Gain may be adjusted through R2. CMRR may be adjusted through R7.

Sine-Wave Oscillator



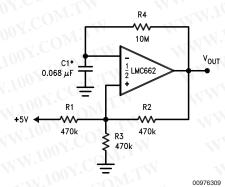
Oscillator frequency is determined by R1, R2, C1, and C2:

$$f_{OSC} = 1/2\pi RC$$

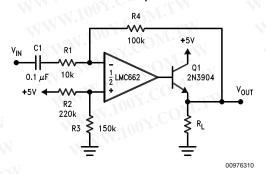
where R = R1 = R2 and C = C1 = C2.

This circuit, as shown, oscillates at 2.0 kHz with a peak-to-peak output swing of $4.5\mathrm{V}$

1 Hz Square-Wave Oscillator



Power Amplifier



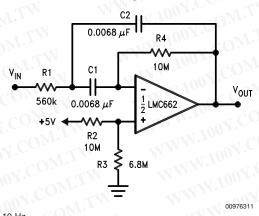
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Typical Single-Supply Applications

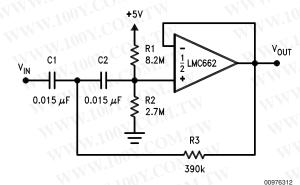
 $(V^+ = 5.0 V_{DC})$ (Continued)

10 Hz Bandpass Filter



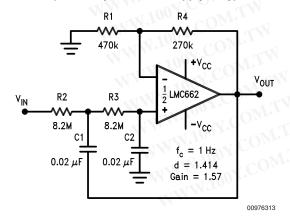
 $f_{O} = 10 \text{ Hz}$ Q = 2.1Gain = -8.8

10 Hz High-Pass Filter

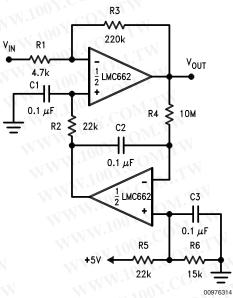


 $f_c = 10 \text{ Hz}$ d = 0.895 Gain = 12 dB passband ripple

1 Hz Low-Pass Filter (Maximally Flat, Dual Supply Only)



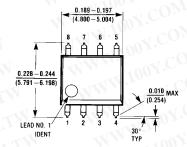
High Gain Amplifier with Offset Voltage Reduction

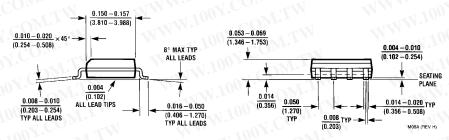


Gain = -46.8

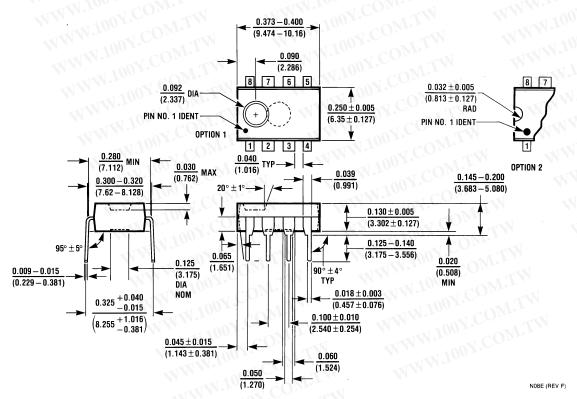
Output offset voltage reduced to the level of the input offset voltage of the bottom amplifier (typically 1 mV).

Physical Dimensions inches (millimeters) unless otherwise noted





Small Outline Dual-In-Line Pkg. (M)
Order Number LMC662AIM, LMC662CM, LMC662AIMX or LMC662CMX
NS Package Number M08A



Molded Dual-In-Line Pkg. (N)
Order Number LMC662AIN, LMC662CN
NS Package Number N08E